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## NPN SILICON PLANAR POWER TRANSISTOR

2N3773



TO-3 Metal Can Package

## Complementary 2N6609

## General Purpose Amplifier specially suited for Power Conditioning Applications

#### **ABSOLUTE MAXIMUM RATINGS**

| DESCRIPTION                              | SYMBOL           | VALUE        | UNITS |
|--|------------------|--------------|-------|
| Collector Base Voltage                   | $V_{CBO}$        | 160          | V     |
| Collector Emitter Voltage                | V <sub>CEO</sub> | 140          | V     |
| Collector Emitter Voltage                | V <sub>CEX</sub> | 160          | V     |
| Emitter Base Voltage                     | $V_{EBO}$        | 7            | V     |
| Collector Current Continuous             | I <sub>C</sub>   | 16           | Α     |
| Peak (1)                                 |                  | 30           | Α     |
| Base Current Continuous                  | I <sub>B</sub>   | 4            | А     |
| Peak (1)                                 |                  | 15           | Α     |
| Power Dissipation @ T <sub>c</sub> =25°C | P <sub>D</sub>   | 150          | W     |
| Derate Above 25°C                        |                  | 0.855        | W/°C  |
| Operating and Storage Junction           | $T_{j},T_{stg}$  | - 65 to +200 | °C    |
| Temperature Range                        |                  |              |       |

### THERMAL RESISTANCE

|                  | _             |      |      |
|------------------|---------------|------|------|
| Junction to Case | $R_{th(j-c)}$ | 1.17 | °C/W |

<sup>(1)</sup> Pulse Test: Pulse Width =5ms, Duty Cycle≤10%

## ELECTRICAL CHARACTERISTICS (T<sub>C</sub>=25°C unless specified otherwise)

| DESCRIPTION                          | SYMBOL                   | TEST CONDITION   | MIN | MAX | UNITS |
|--------------------------------------|--------------------------|--|-----|-----|-------|
| Collector Emitter Sustaing Voltage   | V <sub>CEO (sus)</sub> * | I <sub>C</sub> =0.2A, I <sub>B</sub> =0                        | 140 |     | V     |
| Collector Emitter Sustaing Voltage   | V <sub>CEX (sus) *</sub> | $I_{C}$ =0.1A, $R_{BE}$ =100 $\Omega$ , $V_{BE}$ (off)=1.5 $V$ | 160 |     | V     |
| Collector Emitter Sustaing Voltage   | V <sub>CER (sus)</sub> * | $I_{C}$ =0.2A, $R_{BE}$ =100 $\Omega$                          | 150 |     | V     |
| Collector Cut Off Current            | ρEO                      | $V_{CE}$ =120V, $I_{B}$ =0                                     |     | 10  | mA    |
| Collector Cut Off Current            | PEX                      | V <sub>CE</sub> =140V, V <sub>BE</sub> (off)=1.5V              |     | 2.0 | mA    |
|                                      |                          | T <sub>c</sub> =150°C  |     |     |       |
|                                      |                          | V <sub>CE</sub> =140V, V <sub>BE</sub> (off)=1.5V              |     | 10  | mA    |
| Collector Cut Off Current            | Сво                      | V <sub>CB</sub> =140V, I <sub>E</sub> =0                       |     | 2.0 | mA    |
| Emitter Cut Off Current              | <b>Е</b> во              | $V_{BE}=7V$ , $I_{C}=0$  |     | 5.0 | mA    |
| DC Current Gain                      | h <sub>FE</sub> *        | $I_C=8A, V_{CE}=4V$  | 15  | 60  |       |
|                                      |                          | $I_C=16A, V_{CE}=4V$   | 5   |     |       |
| Collector Emitter Saturation Voltage | V <sub>CE(sat)</sub> *   | I <sub>C</sub> =8A, I <sub>B</sub> =800mA                      |     | 1.4 | V     |
|                                      |                          | I <sub>C</sub> =16A, I <sub>B</sub> =3.2A                      |     | 4.0 | V     |
| Base Emitter on Voltage              | $V_{BE(on)}^*$           | I <sub>C</sub> =8A, V <sub>CE</sub> =4V                        |     | 2.2 | V     |

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TO-3 Metal Can Package

## ELECTRICAL CHARACTERISTICS (T<sub>C</sub>=25°C unless specified otherwise)

### **Dynamic Characteristics**

| DESCRIPTION                         | SYMBOL             | MBOL TEST CONDITION                             |     | MAX | UNITS |
|-------------------------------------|--------------------|---|-----|-----|-------|
| Magnitude of Common Emitter         | Ih <sub>fe</sub> l | I <sub>C</sub> =1A, f=50KHz                     | 4.0 |     |       |
| Small Signal,Short Circuit, Forward |                    |   |     |     |       |
| Current Transfer Ratio              |                    |   |     |     |       |
| Small Signal Current Gain           | h <sub>fe</sub>    | I <sub>C</sub> =1A, V <sub>CE</sub> =4V, f=1KHz | 40  |     |       |

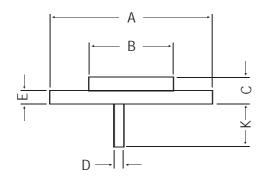
### **Second Breakdown Characteristics**

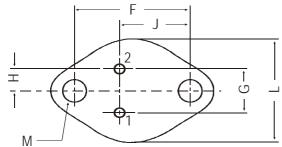
| DESCRIPTION                        | SYMBOL            | TEST CONDITION                                | MIN | MAX | UNITS |
|------------------------------------|-------------------|---|-----|-----|-------|
| Second Breakdown Collector Current | I <sub>S</sub> /b | V <sub>CE</sub> =100V, t=1.0 s, Nonrepetitive | 1.5 |     | Α     |
| With Base Forward Biased           |                   |   |     |     |       |

<sup>\*</sup>Pulse Test: Pulse Width =300ms, Duty Cycle<2%

## **TO-3 Metal Can Package**

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| Α |  |
|---|--|
| В |  |
| С |  |
| D |  |
| Е |  |
| F |  |
| G |  |
| Н |  |
| J |  |
| K |  |
| L |  |
| М |  |
|   |  |

DIM

MIN.

6.35

0.96

29.90

10.69

5.20

16.64

11.15

3.84

MAX.

39.37 22.22

8.50

1.09 1.77

30.40

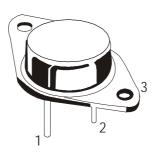
11.18

5.72 17.15

12.25 26.67

4.19

|                      | L |
|----------------------|---|
|                      | Г |
|                      | Г |
|                      | Г |
|                      |   |
| mm.                  | Г |
| in                   | Г |
| ons                  |   |
| ensi                 |   |
| II dimensions in mm. |   |
| Allo                 |   |
|                      | _ |



## PIN CONFIGURATION

- 1. BASE
- 2. EMITTER
- 3. COLLECTOR

# **Packing Detail**

| PACKAGE | STANDARD PACK |                | INNER CARTON BOX  |      | OUTER CARTON BOX  |     |          |
|---------|---------------|----------------|-------------------|------|-------------------|-----|----------|
|         | Details       | Net Weight/Qty | Size              | Qty  | Size              | Qty | Gr Wt    |
| TO-3    | 100 pcs/pkt   | 1.3 kg/100 pcs | 12.5" x 8" x 1.8" | 0.1K | 17" x 11.5" x 21" | 2K  | 27.5 kgs |

Notes 2N3773

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#### **Disclaimer**

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